Abstracts

Super Low Noise AlGaAs/GaAs HEMT with One Tenth Micron Gate

H. Kawasaki, T. Shino, M. Kawano and K. Kamei. "Super Low Noise AlGaAs/GaAs HEMT with One Tenth Micron Gate." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 423-425.

Low noise AIGaAs/GaAs HEMT with 0.1 µm gate length have been successfully developed. A state-of-the-art low noise figure of 0.51 dB and 1.9 dB are obtained at 18 GHz and 40 GHz at room temperature, with an associated gain of 10.8dB and 5.3dB, respectively. The performance has been achieved by shortening the gate length to 0.1 µm and also by lowering the gate resistance drastically with a T shaped gate structure.

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